Hi-Rel EEPROM MCP
Part Matrix

W X E XXX X XXX XX - XXX XXX X X X

MICROSEMI CORPORATION — 1 position

Blank = Multi-Chip Package — 1 position
M = Monolithic

EEPROM — 1 position

Number of Words — 3 (2, 1) positions

Word Factor — 1 position
K = Kilo
M = Mega

Bits per Word — 3 (2, 1) positions

Improvement Mark — 2 (1) positions
N = No Connect for HIP only
P = Alternate Pin Configuration for HIP Package

Access Times (ns) — 3 (2, 1) positions

Package Type/Pin Configuration — 3 (2, 1) positions
C = DIP (32 pin for x8 devices, 40 pin for x16 devices.)
DE = 32 SOJ (Evolutionary)
G2T = 68 CQFP (0.88” sq., 0.180” high)
G1U = 68 CQFP (0.94” sq., 0.140” high)
G1T = 68 CQFP (0.94” sq., 0.160” high)
G4 = 68 CQFP (1.56” sq., 0.200” high)
H1 = 68 PGA (HIP) (1.075” high)

Device Grade — 1 position
Q = MIL-PRF-38534 Compliant
M = Military Screened -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

Special Processing — 1 position

Lead Finish — 1 position
Blank = Gold plated leads
A = Solder Dip leads

Note:
Not all packages, speeds and other options are available on every product.
Please refer to the individual data sheet for option selection.

© 2011 Microsemi Corporation. All rights reserved.